

GRINDING METHOD

ABSTRACT

A grinding method of grinding a first surface side of a wafer having an oxide film on the first surface includes a first grinding step of putting a grinding unit into grinding feeding while rotating a grinding wheel, rotating a chuck table holding under suction a second surface side at a first rotating speed, thereby causing lower surfaces of grindstones to break through the oxide film, then scraping off the oxide film by side surfaces of the grindstones, and forming a step in a circumferential direction of the wafer, a grinding unit raising step of spacing the grindstones from the wafer, and a second grinding step of putting the grinding unit into grinding feeding while rotating the grinding wheel to grind the wafer, in a state in which the chuck table holding under suction a second surface is rotated at a second rotating speed higher than the first rotating speed.

[Fig. 5A]